



March 2, 2008

TriQuint Semiconductor Introduces LDMOS RF Power Transistor Product Portfolio At China IIC Show

TriQuint Adds 35 LDMOS RF Power Transistors for Wireless Base Stations to its Extensive Power, Filter Portfolio

SHENZHEN, CHINA & HILLSBORO, OR (USA) – March 3rd, 2008 – TriQuint Semiconductor (Nasdaq: TQNT), a leading RF semiconductor manufacturer and foundry services provider, today announced its broad portfolio of RF power transistors based on LDMOS (laterally diffused metal oxide semiconductor) technology will now be available world-wide and in China through its Shenzhen and Shanghai offices as well as Avnet Asia Pacific. The wide selection of devices offers manufacturers high-performance, cost-competitive solutions for their RF power amplifier designs.

TriQuint's new RF power transistor line includes products marketed previously by Peak Devices, Boulder, Colorado (USA), that were acquired by TriQuint Semiconductor in August, 2007. This substantial LDMOS power transistor line complements TriQuint's extensive selection of transistors, amplifiers, switch and filter devices for wireless handsets and networked RF communications applications already marketed throughout China.

"We are pleased to expand our product offering for Chinese manufacturers," said Richard Lin, Asia Sales Director. "The new devices added to the TriQuint portfolio cover frequencies from 865MHz to 2.7GHz with RF output power from 30 Watts up to 180 Watts using LDMOS technology. Through offices in Shenzhen and Shanghai, and through Avnet Asia Pacific, manufacturers now have access to one of the most complete and diverse portfolios for their RF, power, filter and switching needs."

TriQuint's new RF power transistor line was introduced in Shenzhen, China today during the 13th Annual International IC-China Conference and Exhibition. Each year this event introduces the latest advancements in electronics engineering to manufacturers and suppliers in major cities across China. The 2008 four-city event began February 28th and will end March 11th; four cities include: Chengdu, Shenzhen, Beijing and Shanghai.

The newly-introduced product portfolio supports the needs of wireless telecommunications base stations and MMDS (multichannel multipoint distribution service) applications, offering a local, reliable source for manufacturers supporting China's continued telecommunications expansion.

Growth of China's wireless networks continues to set records. China now has more mobile subscribers than most countries have citizens (330 million in mid-2007 and growing rapidly.) Governmental decisions to encourage market entry by foreign vendors will bolster growth, according to an iSuppli research forecast¹ that China's 3G value-added services market will grow to \$19.5 billion in 2011.

RF power transistors based on silicon LDMOS remain among the most popular for signal amplification in RF systems due to their high linearity, gain and efficiency, combined with cost-effectiveness born of multiple developmental generations in the commercial market. These new products complement TriQuint's gallium arsenide (GaAs) transistors, amplifiers and switches as well as surface acoustic and bulk acoustic wave (SAW / BAW) filters now marketed across China.

"Customers now have more choices: the cost-effective, high performance of LDMOS as well as the advantages of highly-efficient, highly-linear GaAs devices that enable the RF engineer to simplify product decisions around customer needs," remarked Mr. Lin.

The new LDMOS product line is available now in China and worldwide through TriQuint's network of direct and representative salespeople. For a detailed list of TriQuint RF products, visit www.triquint.com/china or www.triquint.com and register for new product details at www.triquint.com/china/rf or www.triquint.com/rf. To contact Avnet Asia Pacific, visit: <http://www.avnet.com/home>.

¹ As reported in a July 27, 2007 EE Times magazine article.

FORWARD LOOKING STATEMENTS

This TriQuint Semiconductor, Inc. (Nasdaq: TQNT) press release contains forward-looking statements made pursuant to the

Safe Harbor provisions of the Private Securities Litigation Reform Act of 1995. Readers are cautioned that forward-looking statements involve risks and uncertainties. The cautionary statements made in this press release should be read as being applicable to all related statements wherever they appear. Statements containing such words as 'leading', 'exceptional', 'high efficiency', 'adding value', 'leading supplier', or similar terms are considered to contain uncertainty and are forward-looking statements. A number of factors affect TriQuint's operating results and could cause its actual future results to differ materially from any results indicated in this press release or in any other forward-looking statements made by, or on behalf of, TriQuint including, but not limited to: those associated with the unpredictability and volatility of customer acceptance of and demand for our products and technologies, the ability of our production facilities and those of our vendors to meet demand, the ability of our production facilities and those of our vendors to produce products with yields sufficient to maintain profitability, as well as the other "Risk Factors" set forth in TriQuint's most recent 10-Q report filed with the Securities and Exchange Commission. This and other reports can be found on the SEC web site, www.sec.gov. A reader of this release should understand that these and other risks could cause actual results to differ materially from expectations expressed / implied in forward-looking statements.

FACTS ABOUT TRIQUINT

Founded in 1985, we "Connect the Digital World to the Global Network"™ by supplying high performance RF modules, components and foundry services to the world's leading communications companies. Specifically, TriQuint supplies products to four out of the top five cellular handset manufacturers, and is a leading gallium arsenide (GaAs) supplier to major defense and space contractors. TriQuint creates standard and custom products using advanced processes that include gallium arsenide, surface acoustic wave (SAW) and bulk acoustic wave (BAW) technologies to serve diverse markets including wireless handsets, base stations, broadband communications and military. TriQuint is also lead researcher in a 3-year DARPA program to develop advanced gallium nitride (GaN) amplifiers. TriQuint, as named by Strategy Analytics in August 2007, is the number-three worldwide leader in GaAs devices and the world's largest commercial GaAs foundry. TriQuint has ISO9001 certified manufacturing facilities in Oregon, Texas, and Florida and a production plant in Costa Rica; design centers are located in North America and Germany. Visit TriQuint at www.triquint.com/rf to register for our newsletters.

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